Low-power dual 2-input NAND Schmitt trigger Rev. 7 — 8 February 2013

Product data sheet

General description 1.

The 74AUP2G132 provides the dual 2-input NAND Schmitt trigger function which accepts standard input signals. They can transform slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Applications 3.

- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator



Low-power dual 2-input NAND Schmitt trigger

4. Ordering information

Table 1. Ordering	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G132DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G132GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G132GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089
74AUP2G132GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2
74AUP2G132GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2
74AUP2G132GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AUP2G132GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203

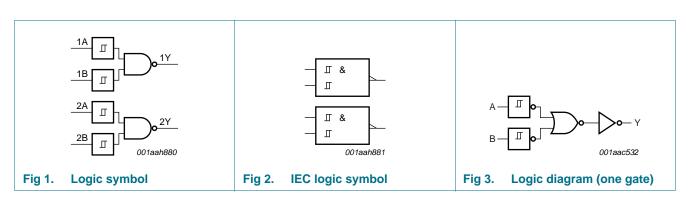
5. Marking

Table 2.Marking codes

5	
Type number	Marking code ^[1]
74AUP2G132DC	aE2
74AUP2G132GT	aE2
74AUP2G132GF	aE
74AUP2G132GD	aE2
74AUP2G132GM	aE2
74AUP2G132GN	aE
74AUP2G132GS	aE

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram

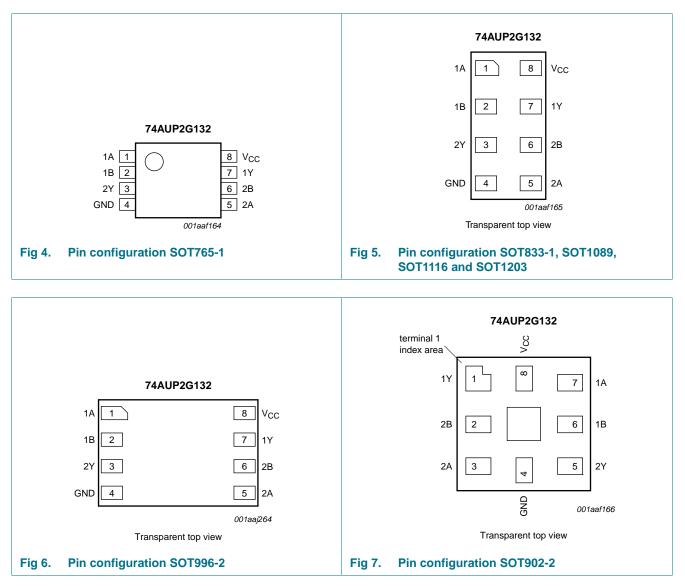


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Low-power dual 2-input NAND Schmitt trigger

7. Pinning information

7.1 Pinning



7.2 Pin description

Symbol	Pin		Description	
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V _{CC}	8	8	supply voltage	
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Product data	sheet Rev.	7 — 8 February 20	013	3 of 23

Low-power dual 2-input NAND Schmitt trigger

8. Functional description

Table 4.	Function table ^[1]		
Input			Output
nA		nB	nY
L		L	н
L		Н	Н
Н		L	Н
Н		Н	L
-			

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Ι _Ο	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $\ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C

74AUP2G132 Product data sheet

Low-power dual 2-input NAND Schmitt trigger

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = 2	5 °C					
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		$I_0 = 20 \ \mu$ A; $V_{CC} = 0.8 \ V$ to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
1	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μA
OFF	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.2	μΑ
∆I _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
СС	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
VICC	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	40	μA
C _I	input capacitance	$V_{I} = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	1.1	-	pF
\mathcal{S}_{0}	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
	40 °C to +85 °C					
/ _{он}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
0.11		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V}$	$V_{CC} - 0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_0 = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{\rm O} = -2.3 \text{ mA; } V_{\rm CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	_	-	V
			2.00			v

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74AUP2G132

Low-power dual 2-input NAND Schmitt trigger

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_I = V_{T+} \text{ or } V_{T-}$				
		I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.9	μA
Δl _{CC}	additional supply current		[1] -	-	50	μA
T _{amb} = –	40 °C to +125 °C					
V _{ОН}	HIGH-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
lı	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μA

Static characteristics ... continued Table 7.

Low-power dual 2-input NAND Schmitt trigger

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current		<u>[1]</u> -	-	75	μΑ

Table 7. Static characteristics ...continued

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

12. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

Symbol	Parameter	Conditions	Ta	_{mb} = 25	°C	T _{amb} =	-40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pF	F								
t _{pd}	propagation delay	nA or nB to nY; see <u>Figure 8</u>	[2]						
		$V_{CC} = 0.8 V$	-	22.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2.6	6.3	13.4	2.4	15.1	16.6	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.2	4.6	8.2	1.9	9.7	10.7	ns
		V_{CC} = 1.65 V to 1.95 V	1.9	3.9	6.6	1.7	7.9	8.7	ns
		V_{CC} = 2.3 V to 2.7 V	1.7	3.2	5.3	1.5	6.2	6.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.6	2.9	4.7	1.4	5.6	6.2	ns
C _L = 10 p	ρF								
t _{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]						
		$V_{CC} = 0.8 V$	-	26.1	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.0	7.2	15.4	2.7	17.3	19.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.5	5.2	9.3	2.2	11.0	12.1	ns
		V_{CC} = 1.65 V to 1.95 V	2.3	4.5	7.5	2.0	9.0	9.9	ns
		V_{CC} = 2.3 V to 2.7 V	2.1	3.8	6.1	1.8	7.2	7.9	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	3.5	5.5	1.8	6.5	7.2	ns
C _L = 15 p	ρF								
t _{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]						
		$V_{CC} = 0.8 V$	-	29.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.3	8.0	17.2	3.0	19.4	21.3	ns
		V_{CC} = 1.4 V to 1.6 V	2.8	5.8	10.4	2.5	12.3	13.5	ns
		V_{CC} = 1.65 V to 1.95 V	2.6	5.0	8.3	2.3	10.0	11.0	ns
		V_{CC} = 2.3 V to 2.7 V	2.3	4.2	6.7	2.1	7.9	8.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.2	3.9	6.1	2.0	7.3	8.0	

Low-power dual 2-input NAND Schmitt trigger

Symbol	Parameter	Conditions		Ta	_{mb} = 25 °	°C	T _{amb} =	= −40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	_
C _L = 30	pF									
t _{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	39.9	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.3	10.2	22.6	3.8	25.4	27.9	ns
		V_{CC} = 1.4 V to 1.6 V		3.6	7.3	13.3	3.2	15.8	17.4	ns
		V_{CC} = 1.65 V to 1.95 V		3.2	6.3	10.6	2.9	12.8	14.1	ns
		V_{CC} = 2.3 V to 2.7 V		3.0	5.3	8.5	2.7	10.1	11.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.8	5.0	7.8	2.7	9.2	10.1	ns
C _L = 5 p	F, 10 pF, 15 pF and	30 pF								
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]							
	capacitance	$V_{CC} = 0.8 V$		-	2.6	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	2.9	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	3.0	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	3.2	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.8	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.4	-	-	-	-	рF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

[1] All typical values are measured at nominal V_{CC}.

 $\label{eq:tpd} [2] \quad t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

$$\begin{split} N &= number \mbox{ of inputs switching;} \\ \Sigma(C_L \times V_{CC}{}^2 \times f_o) &= sum \mbox{ of the outputs.} \end{split}$$

Low-power dual 2-input NAND Schmitt trigger

13. Waveforms

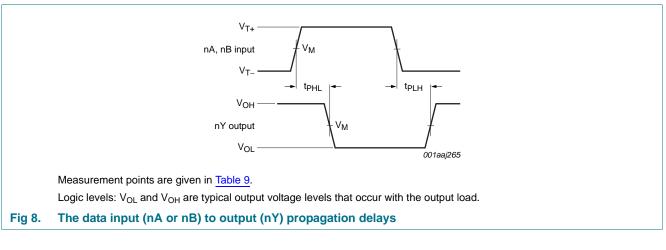


Table 9. Measurement points

Supply voltage	Output	Input					
V _{CC}	V _M	V _M	VI	t _r = t _f			
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	≤ 3.0 ns			

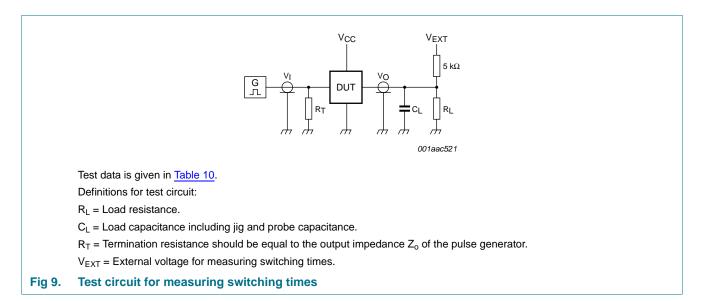


Table 10.Test data

Supply voltage	Load	V _{EXT}			
V _{cc}	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] $R_L = 5 k\Omega$ when measuring enable and disable times. $R_L = 1 M\Omega$ when measuring propagation delays, setup and hold times and pulse width.

74AUP2G132 Product data sheet

Low-power dual 2-input NAND Schmitt trigger

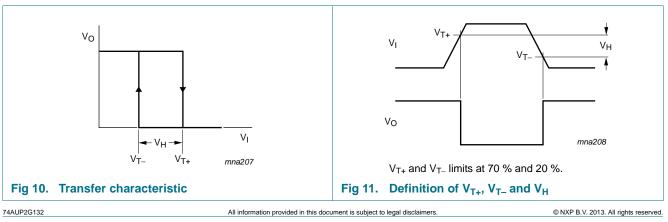
14. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9.

Symbol	Parameter	Conditions	T _{amb} = 25 °C		T _{amb} = -40 °C to +125 °C			Unit	
			Тур	Max	Min	Max (85 °C)	Max (125 °C)		
V_{T+}	V _{T+} positive-going threshold voltage	see <u>Figure 10</u> and <u>Figure 11</u>							
		$V_{CC} = 0.8 V$	0.30	-	0.60	0.30	0.60	0.62	V
		$V_{CC} = 1.1 V$	0.53	-	0.90	0.53	0.90	0.92	V
		$V_{CC} = 1.4 V$	0.74	-	1.11	0.74	1.11	1.13	V
		V _{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		$V_{CC} = 2.3 V$	1.37	-	1.77	1.37	1.77	1.80	V
		$V_{CC} = 3.0 V$	1.88	-	2.29	1.88	2.29	2.32	V
V_{T-}	V _T - negative-going threshold voltage	see <u>Figure 10</u> and <u>Figure 11</u>							
		$V_{CC} = 0.8 V$	0.10	-	0.60	0.10	0.60	0.60	V
		$V_{CC} = 1.1 V$	0.26	-	0.65	0.26	0.65	0.65	V
		$V_{CC} = 1.4 V$	0.39	-	0.75	0.39	0.75	0.75	V
		V _{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		$V_{CC} = 2.3 V$	0.69	-	1.04	0.69	1.04	1.04	V
		$V_{CC} = 3.0 V$	0.88	-	1.24	0.88	1.24	1.24	V
V _H hysteresis voltage	$(V_{T+} - V_{T-})$; see <u>Figure 10</u> , <u>Figure 11</u> , <u>Figure 12</u> and <u>Figure 13</u>								
		$V_{CC} = 0.8 V$	0.07	-	0.50	0.07	0.50	0.50	V
		V _{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		V _{CC} = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V
		V _{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		$V_{CC} = 2.3 V$	0.53	-	0.92	0.53	0.92	0.92	V
		$V_{CC} = 3.0 V$	0.79	-	1.31	0.79	1.31	1.31	V

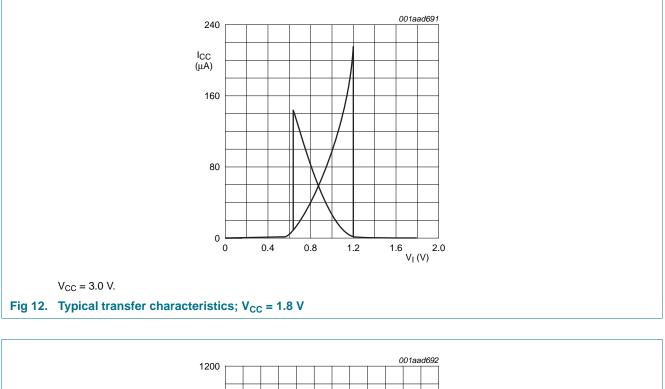
15. Waveforms transfer characteristics

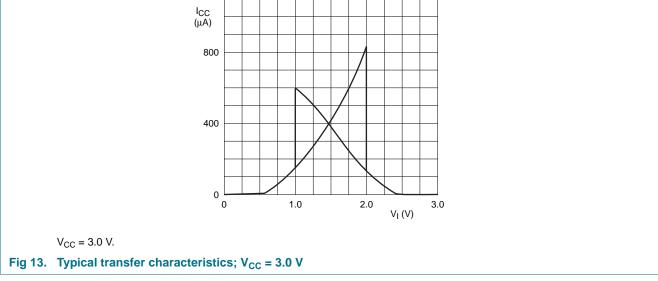


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Low-power dual 2-input NAND Schmitt trigger

16. Application information

The slow input rise and fall times cause additional power dissipation which can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$

 P_{add} = additional power dissipation (μ W);

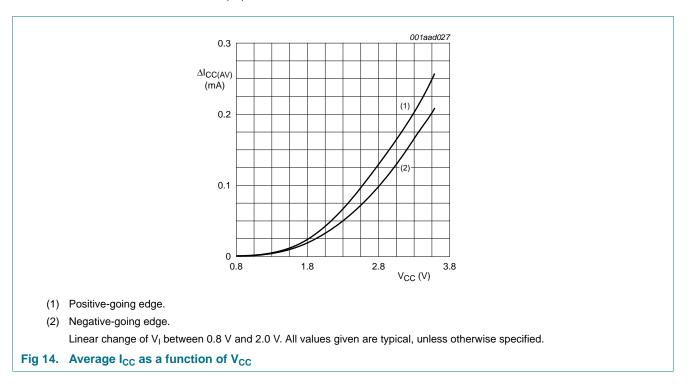
 $f_i = input frequency (MHz);$

 t_r = input rise time (ns); 10 % to 90 %;

 t_f = input fall time (ns); 90 % to 10 %;

 $\Delta I_{CC(AV)}$ = average additional supply current (µA).

Average $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in Figure 14.



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17. Package outline

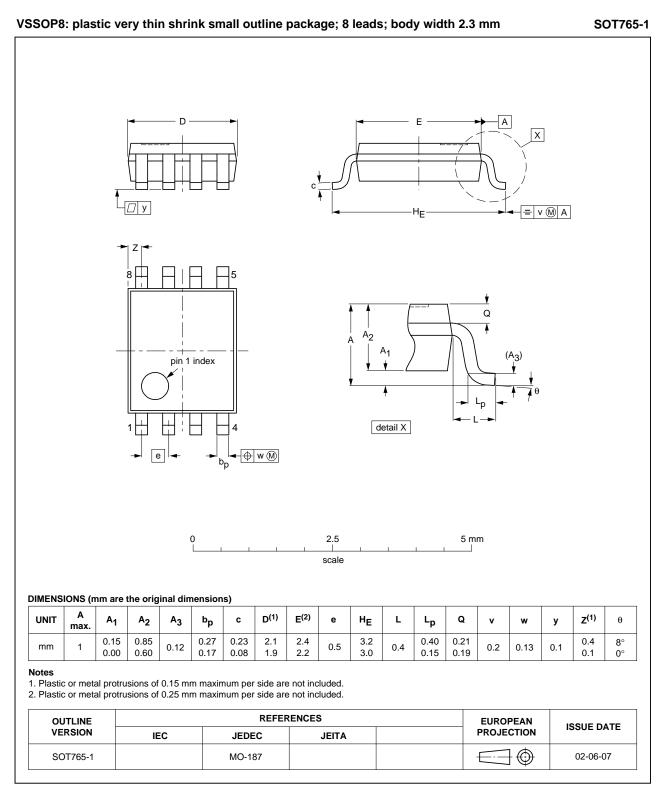


Fig 15. Package outline SOT765-1 (VSSOP8)

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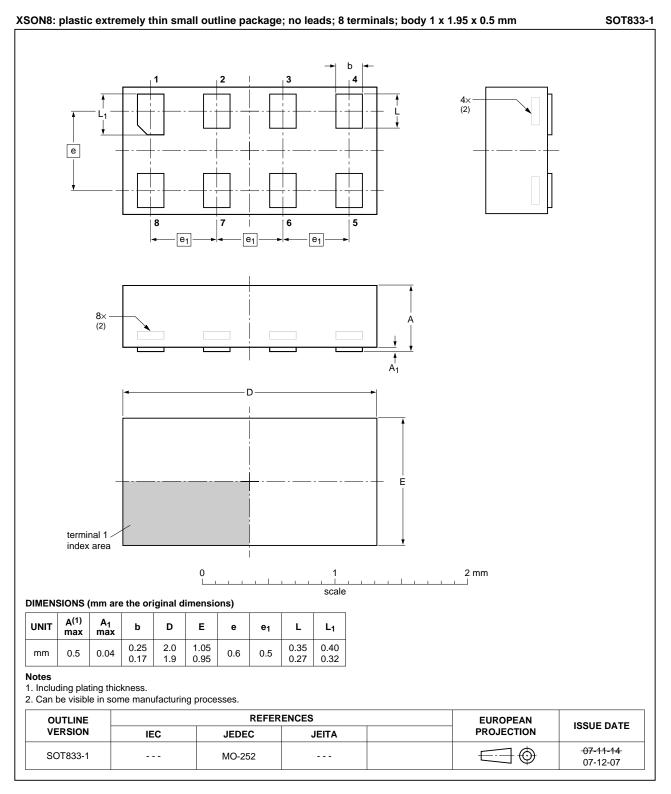
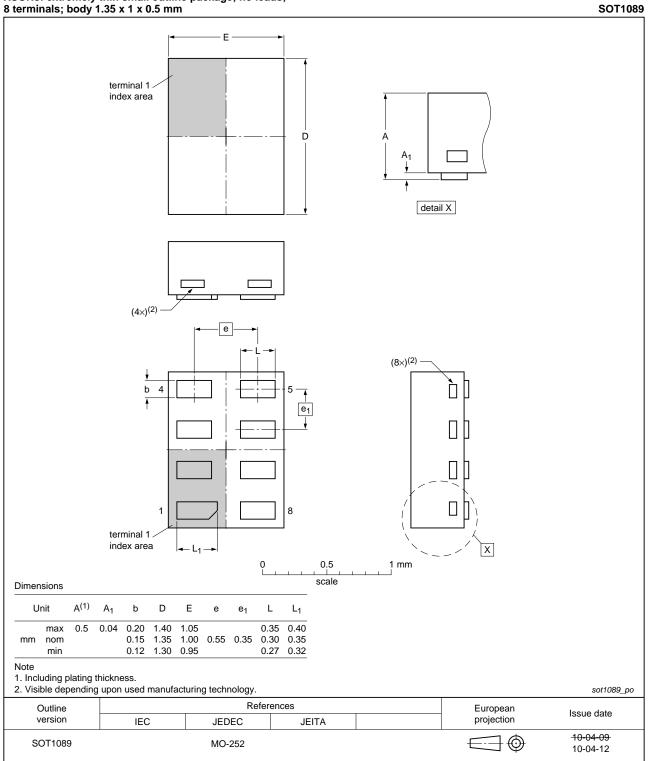


Fig 16. Package outline SOT833-1 (XSON8)

74AUP2G132 Product data sheet

14 of 23

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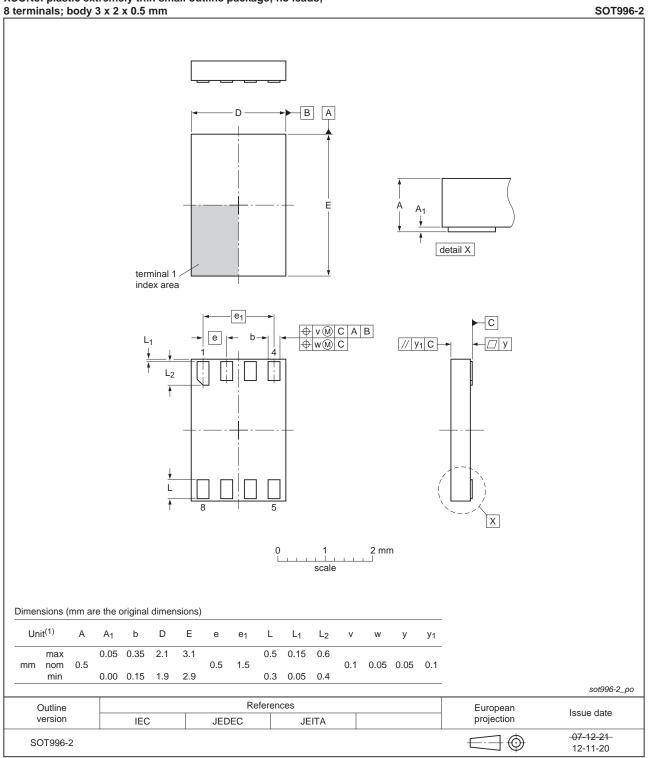


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 17. Package outline SOT1089 (XSON8)

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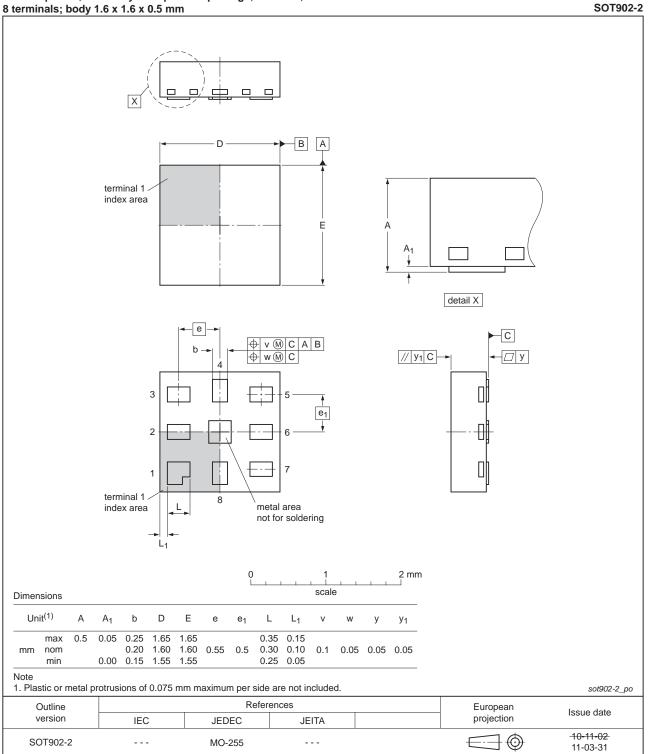


XSON8: plastic extremely thin small outline package; no leads;

Fig 18. Package outline SOT996-2 (XSON8)

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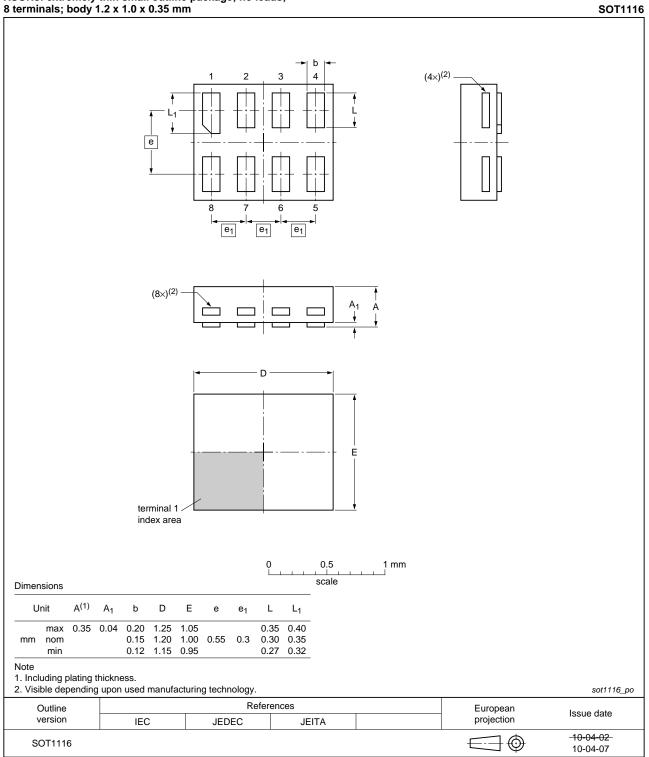


XQFN8: plastic, extremely thin quad flat package; no leads;

Fig 19. Package outline SOT902-2 (XQFN8)

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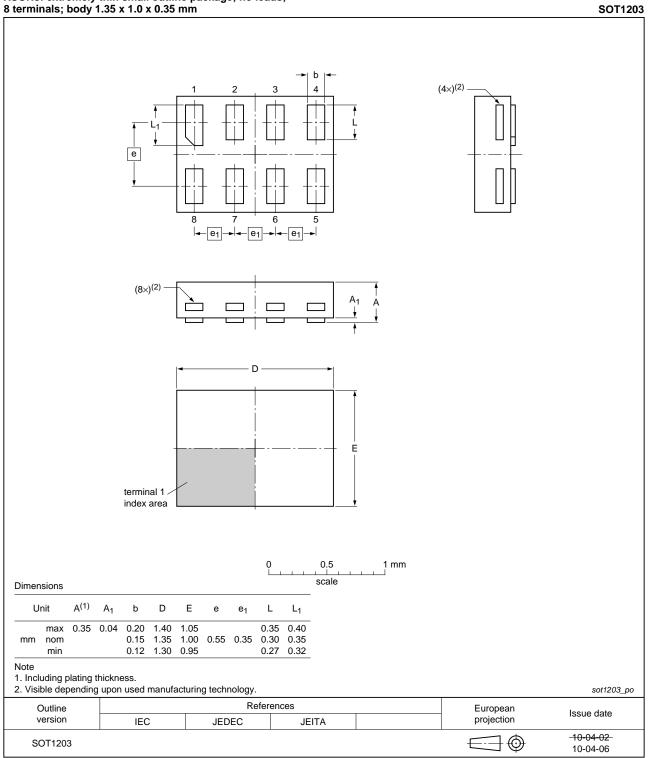
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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 20. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 21. Package outline SOT1203 (XSON8)

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18. Abbreviations

Table 12. Abbreviations			
Acronym	Description		
CDM	Charged Device Model		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
НВМ	Human Body Model		
MM	Machine Model		

19. Revision history

Document IDRelease dateData sheet statusChange noticeSupersedes74AUP2G132 v.720130208Product data sheet-74AUP2G132 v.6Modifications:• For type number 74AUP2G132GD XSON8U has changed to XSON8.74AUP2G132 v.620120803Product data sheet-74AUP2G132 v.574AUP2G132 v.520111201Product data sheet-74AUP2G132 v.474AUP2G132 v.420101104Product data sheet-74AUP2G132 v.374AUP2G132 v.320081215Product data sheet-74AUP2G132 v.274AUP2G132 v.220080314Product data sheet-74AUP2G132 v.1	Table 13. Revision h	istory			
Modifications:• For type number 74AUP2G132GD XSON8U has changed to XSON8.74AUP2G132 v.620120803Product data sheet-74AUP2G132 v.574AUP2G132 v.520111201Product data sheet-74AUP2G132 v.474AUP2G132 v.420101104Product data sheet-74AUP2G132 v.374AUP2G132 v.320081215Product data sheet-74AUP2G132 v.2	Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G132 v.6 20120803 Product data sheet - 74AUP2G132 v.5 74AUP2G132 v.5 20111201 Product data sheet - 74AUP2G132 v.4 74AUP2G132 v.4 20101104 Product data sheet - 74AUP2G132 v.3 74AUP2G132 v.3 20081215 Product data sheet - 74AUP2G132 v.2	74AUP2G132 v.7	20130208	Product data sheet	-	74AUP2G132 v.6
74AUP2G132 v.5 20111201 Product data sheet - 74AUP2G132 v.4 74AUP2G132 v.4 20101104 Product data sheet - 74AUP2G132 v.3 74AUP2G132 v.3 20081215 Product data sheet - 74AUP2G132 v.2	Modifications:	 For type nur 	mber 74AUP2G132GD XS	ON8U has changed to X	(SON8.
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	74AUP2G132 v.4	20101104	Product data sheet	-	74AUP2G132 v.3
74AUP2G132 v.2 20080314 Product data sheet - 74AUP2G132 v.1	74AUP2G132 v.3	20081215	Product data sheet	-	74AUP2G132 v.2
	74AUP2G132 v.2	20080314	Product data sheet	-	74AUP2G132 v.1
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22. Contents

1	General description 1
2	Features and benefits 1
3	Applications 1
4	Ordering information 2
5	Marking 2
6	Functional diagram 2
7	Pinning information 3
7.1	Pinning 3
7.2	Pin description 3
8	Functional description 4
9	Limiting values 4
10	Recommended operating conditions 4
11	Static characteristics 5
12	Dynamic characteristics 7
13	Waveforms
14	Transfer characteristics 10
15	Waveforms transfer characteristics 10
16	Application information
17	Package outline
18	Abbreviations
19	Revision history
20	Legal information
20.1	Data sheet status 21
20.2	Definitions
20.3	Disclaimers 21
20.4	Trademarks 22
21	Contact information 22
22	Contents 23

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